

ELEC2208 Power Electronics and Drives

Extra slides

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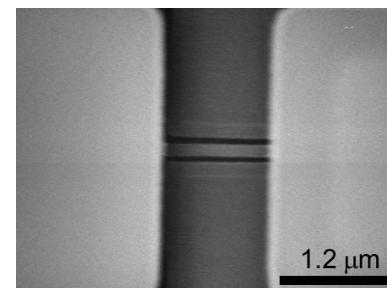
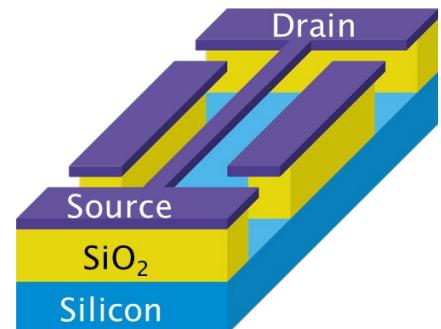
My research link with Power Electronics

Topic

Nanoelectromechanical Systems (NEMS)

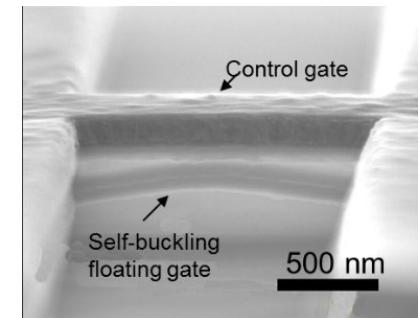
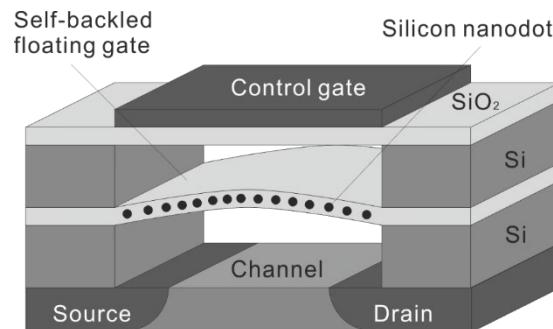
NEMS Resonator

Y. Tsuchiya et al., IEEE MEMS2018



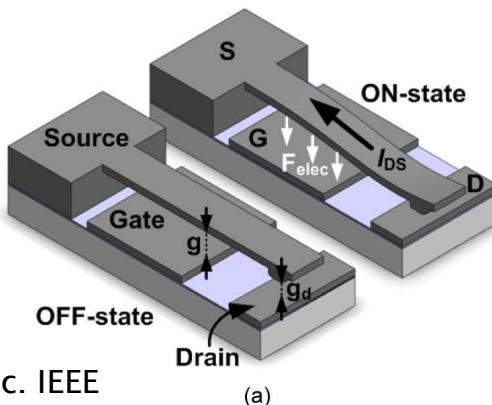
NEMS memory

Y. Tsuchiya et al, JAP 2006

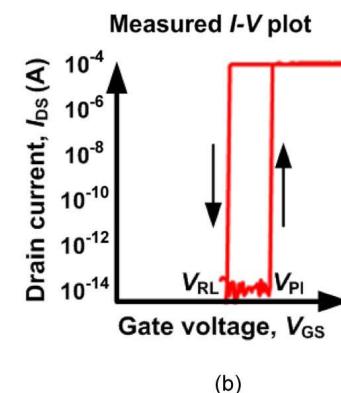


MEMS/NEMS switches for power management → Towards “Ideal switch”!

Contact switches

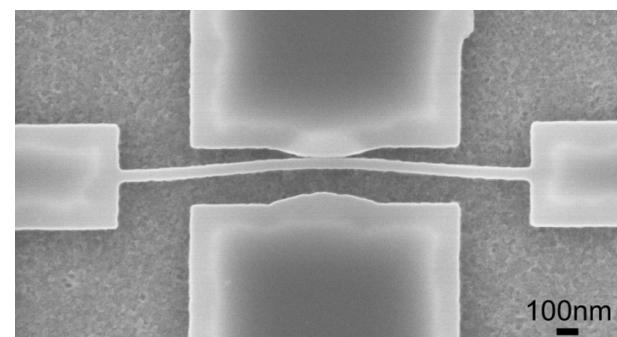


V. Pott et al., Proc. IEEE
98, 2076 (2010).



Energy-reversible low-power NEMS switches

Boodhoo, Tsuchiya et al.,
Microelec. Eng. 2015.



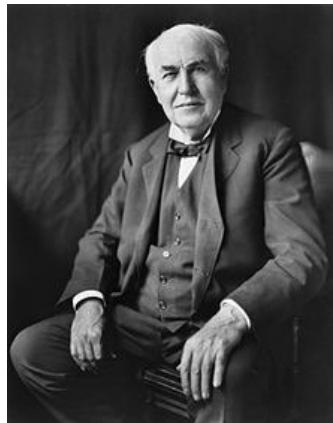
Diode - History

Topic

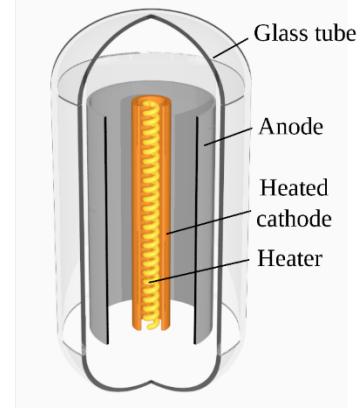


F. Guthrie
British physicist
(1873)

Vacuum tube
diode



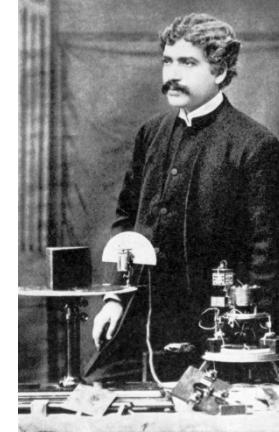
T. Edison
American inventor
(1880)



K. F. Braun
German engineer
(1874)

Solid state diode

Contact between metal and
mineral/crystal



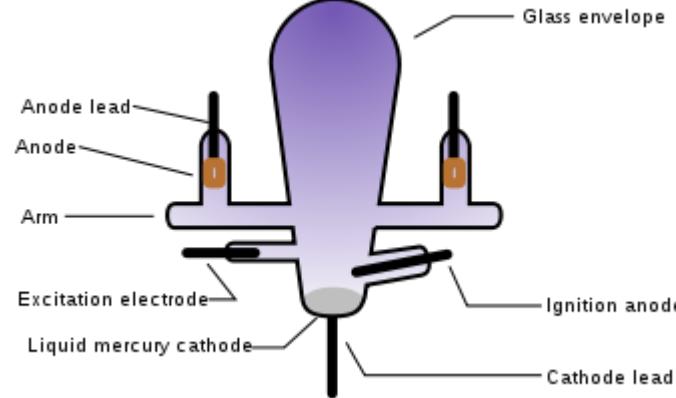
J. C. Bose
Indian scientist
(1894)

Rectifier – History

<https://en.wikipedia.org/wiki/Rectifier>

Topic

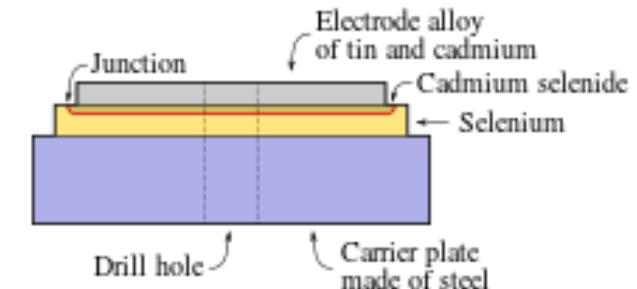
Mercury-arc rectifier



- Invented by American engineer Peter Cooper Hewitt in 1902.
- Cold cathode gas-filled tube.
- For high-voltage and high current.

Then superseded by silicon rectifier in 1970s.

Selenium rectifier



- Manufactured from 1930s
- Metal (CdSe) – Semiconductor (Se) junction

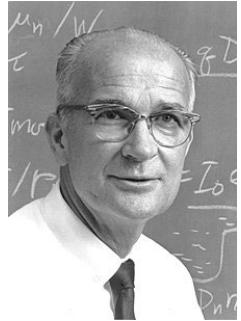


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Thyristor - History

Topic

- PNPN switches developed at Bell laboratories.



Proposal

W. Shockley



Team leader

J. Moll

- Commercialised by General Electric (GE) in 1957.
- “Thyratron” + “Transistor” = “Thyristor”
- Dawn of “Power Electronics”

<https://en.wikipedia.org/wiki/Thyristor>

<https://www.tdworld.com/digital-innovations/hvdc/article/20969683/a-short-history-on-the-thyristor-valve>



Frank “Bill” Gutzwiller



Power MOSFET - History

Topic

MOSFET was invented by Atalla and Kahng at Bell Labs, US in 1959.

Power MOSFET was invented in 1969

- Hitachi invented a basis of VMOS (Vertical MOS)
- Yasuo Tarui et al (ETL, Japan) invented DDMOST (Double-Diffused MOS Transistor)

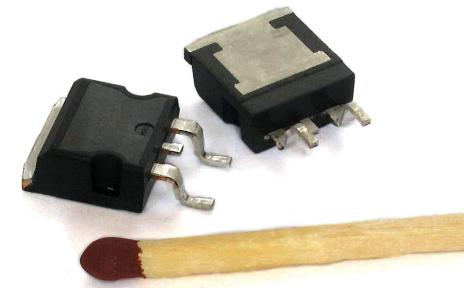
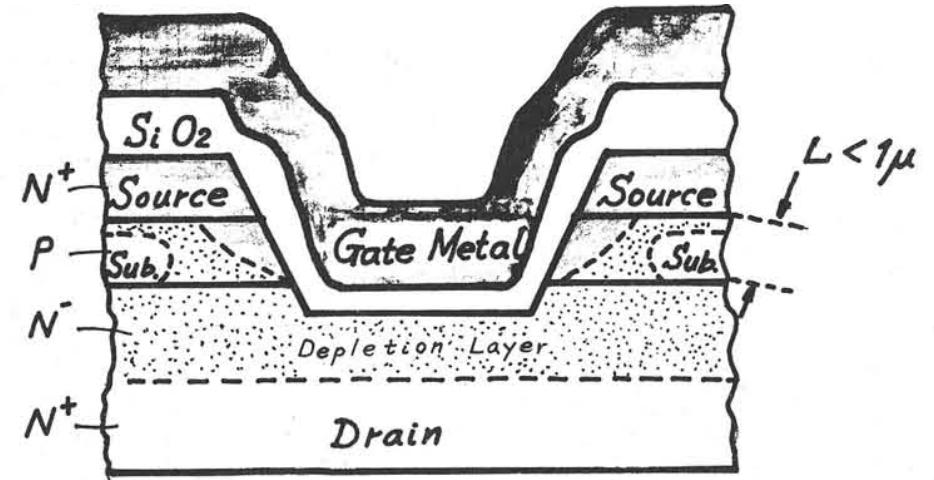
Commercialisation

Siliconix (UK) delivered VMOS in 1975 as the first power FET in the marketplace.

<https://www.electronicdesign.com/content/article/21188215/then-and-now>

https://en.wikipedia.org/wiki/Power_MOSFET

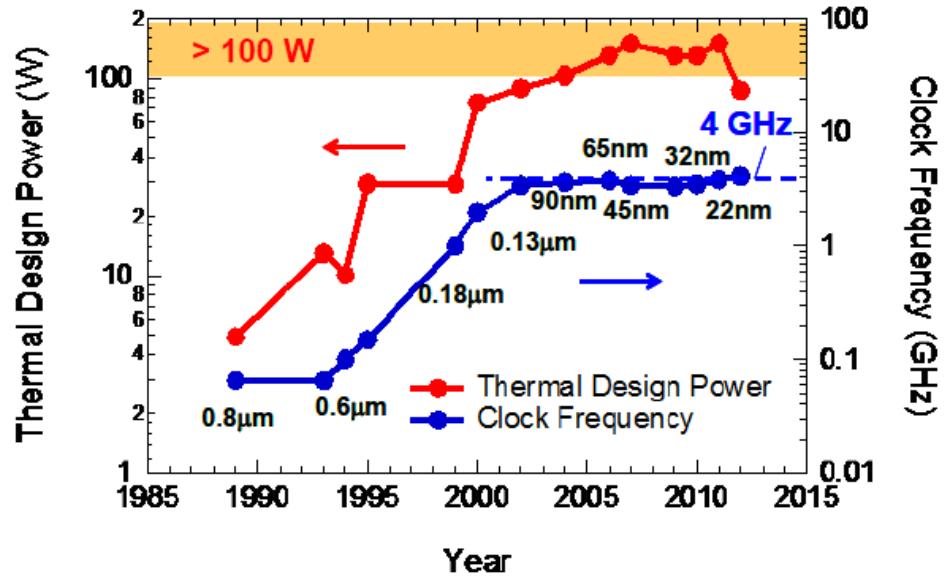
Tarui et al., SSDM 1969



My research link with Power Electronics

Topic

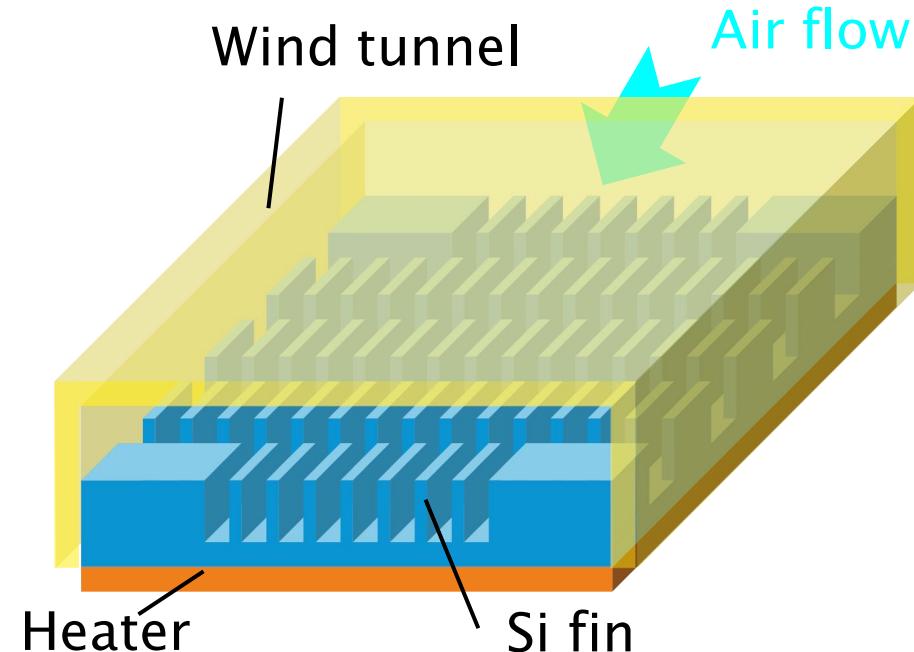
TDP vs Frequency in ICs



- CPU clock frequency capped since early 2000.
- **The performance is limited by heat generation.**

Silicon surface modified heat sinks

Y Zhang, Y Tsuchiya *et al.*, MNE2017, ICAN 2019



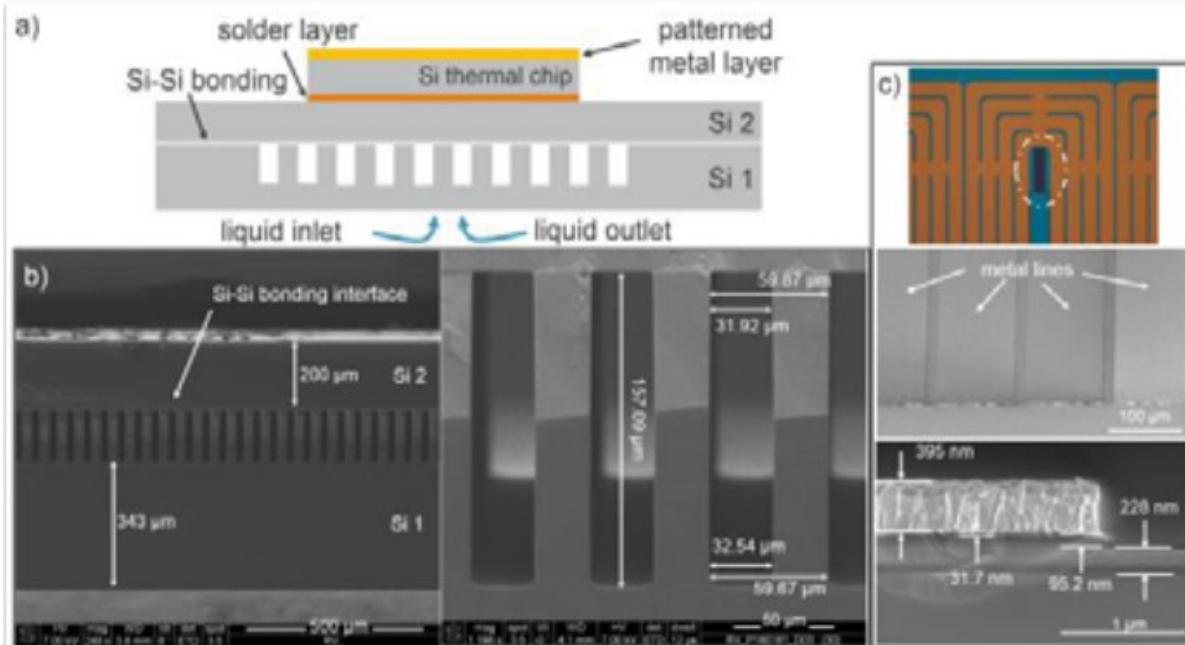
- Surface modification via micro- and nanofabrication technology to reduce the thermal resistance $R_{\theta(s-a)}$.

Embedded cooling trends

Topic

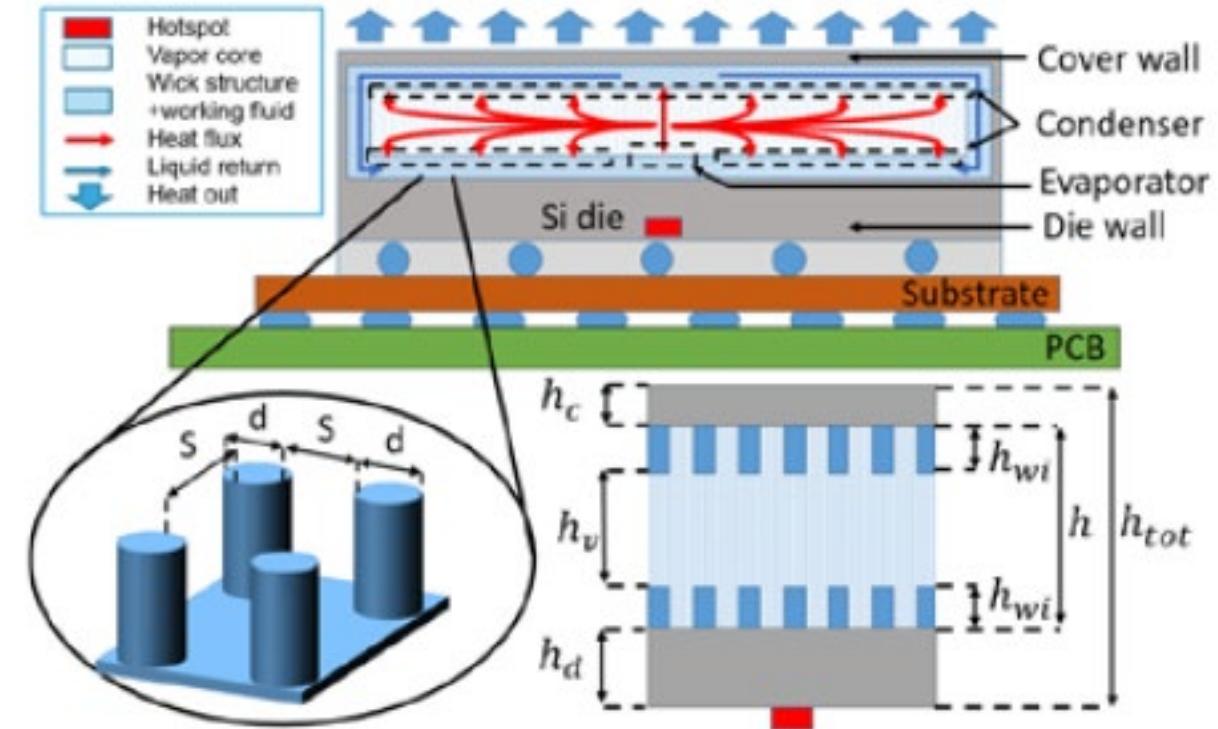
Si microchannels

L Zhang *et al.*, Therminic 2018



Si vapor chamber

Q Struss *et al.*, Therminic 2018



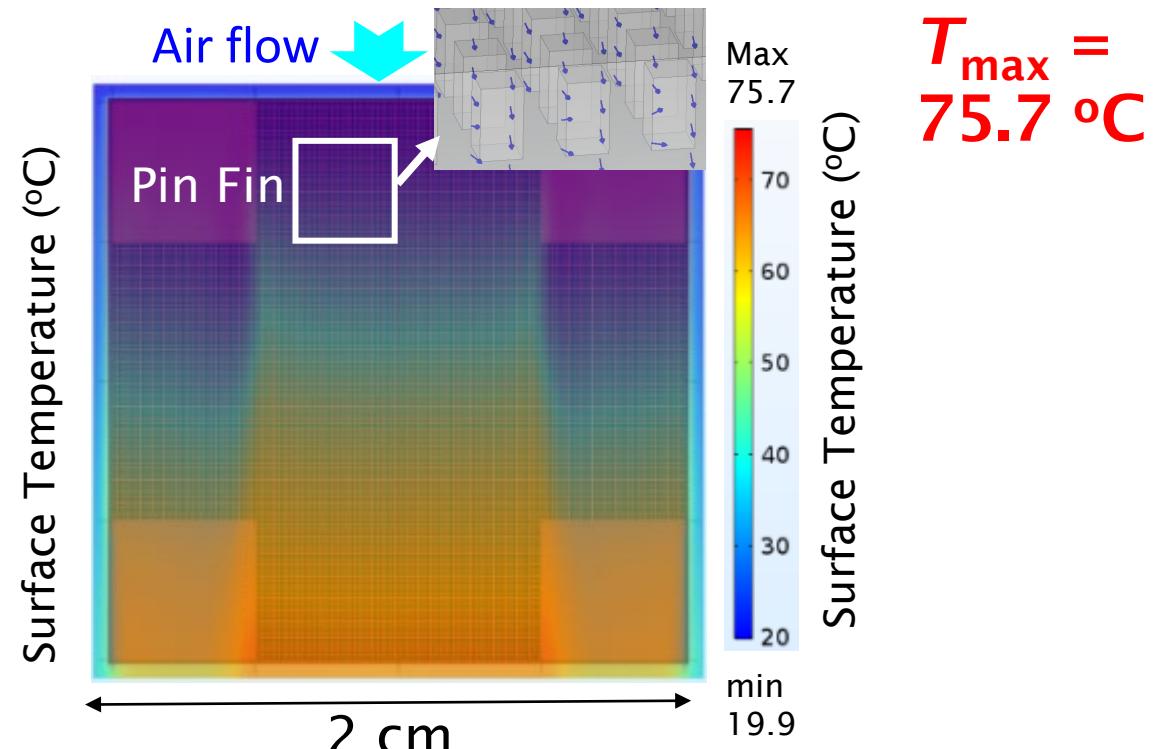
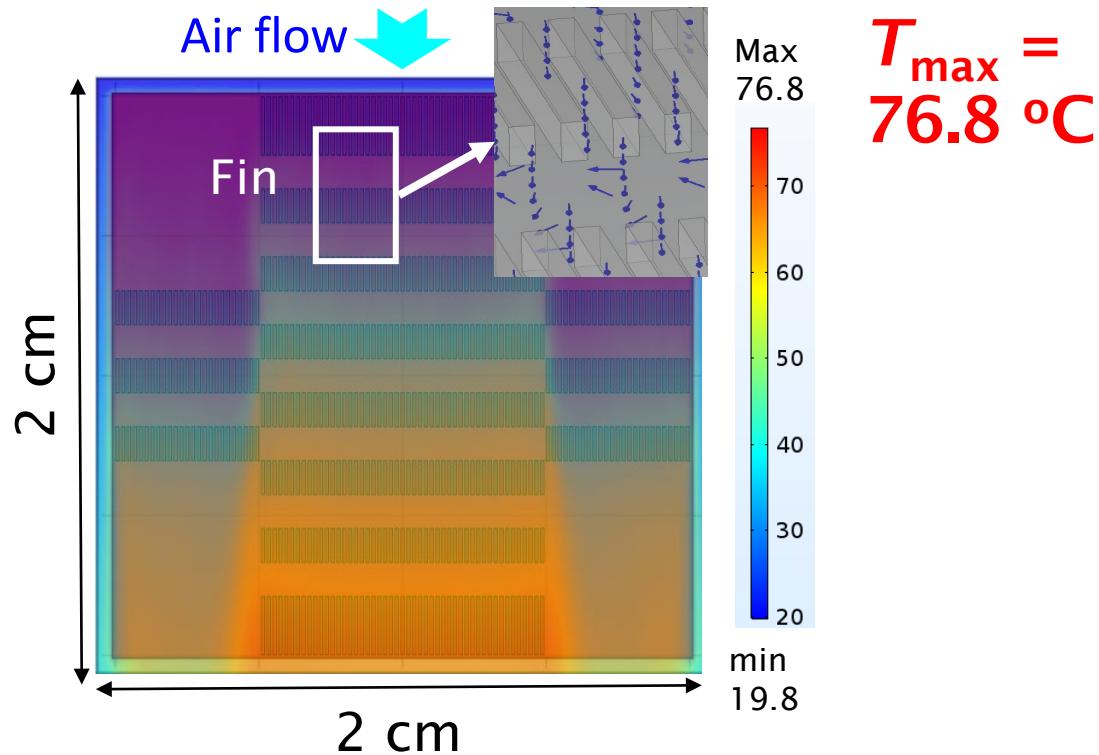
Application of silicon micro- and nanofabrication technologies for electronics cooling is under investigation in research level.

COMSOL simulation results

Topic

Inlet velocity: 3 m/s, Inlet T : 20 °C, Heater power: 3W

Y Zhang, PhD thesis



- Micro pin fin with larger surface area shows better.
- Further design optimisation possible (via movable fins, Al, etc)

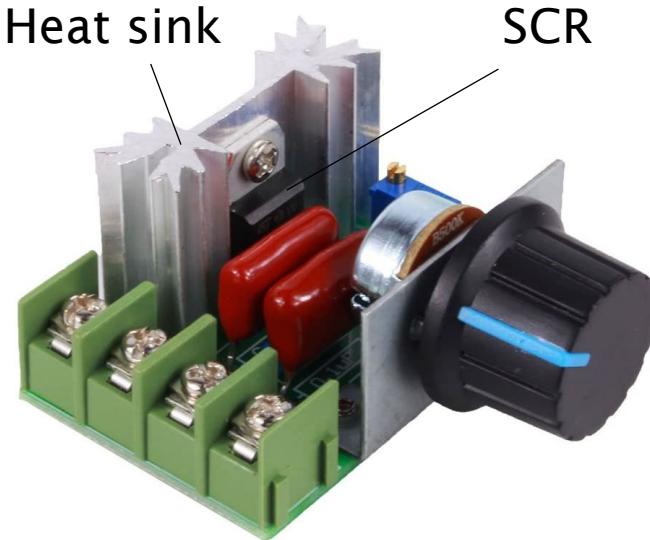
AC voltage controllers - Products

Topic

<https://www.amazon.co.uk/>



220 V 4000 W voltage controller



50-220V LED Dimmer

Practical applications

Light dimmer, Fan controller, Motor controller, Temperature controller, etc.



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AC/DC converters

Topic



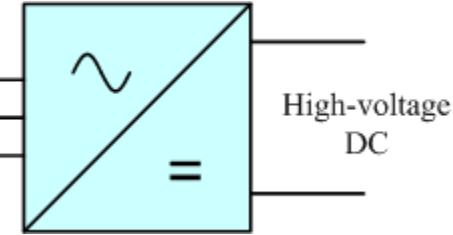
AC/DC adapter

AC 100-240V -> DC 12V



Thyristor Bridge Rectifier Module,
Three Phase, 1600 V

Three-phase
high-voltage
AC



HVDC converter

~ 2000 MW, 900 kV

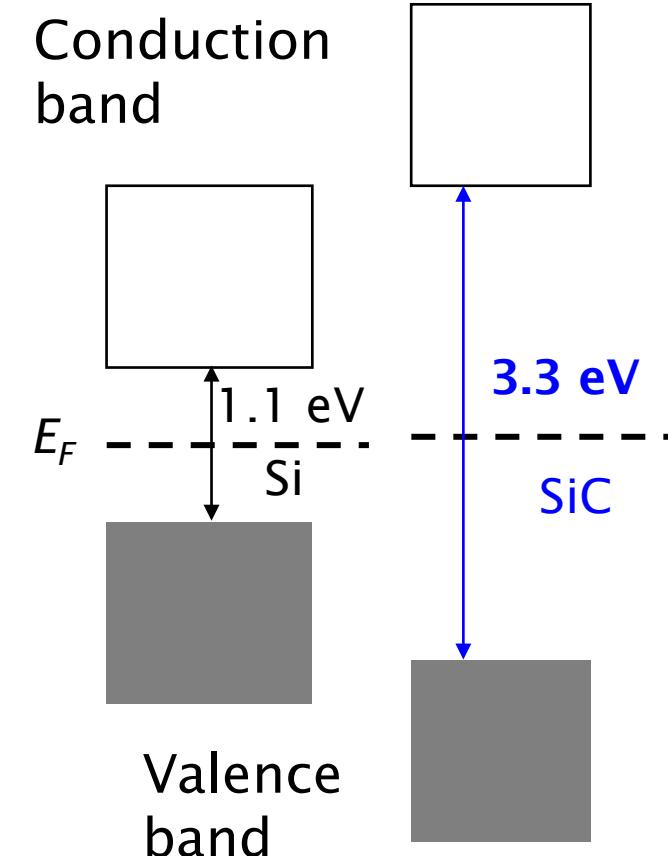


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Wide band-gap Semiconductors

Topic

J. Wang, IOP Conf. Series: Materials Science and Engineering 729 (2020) 012005



	Si	4H-SiC	GaN	$\beta\text{-Ga}_2\text{O}_3$
Band gap, E_g (eV)	1.1	3.3	3.4	4.5
Breakdown field, E_c (MV/cm)	0.25	2.4	3.5	7
Relative permittivity, ϵ	11.8	9.7	9.0	10-12
Electron mobility, μ_e (cm ² /V.s)	1400	950	1200	200
Thermal conductivity (W/cm.K)	1.5	3.3 - 4.9	2	0.27
Baliga's Figure of Merit $\sim \epsilon \mu_e E_g^3$	1	340	870	>1,500

Promising materials for future power electronics and devices.



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Cycloconverter (CCV)

Topic

<https://library.e.abb.com/>

ACS 6000c Cycloconverter



Applications

- Ship propulsion
- Ball mills
- Mine hoists

For cases where load changes gradually.

50/60 Hz -> 0 - 24/28 Hz
Speed and torque control of 1-27 MW

DC-DC converter

Topic

<https://www.mouser.co.uk/>

MEAN WELL

Input 9-36 V
Output 12 V



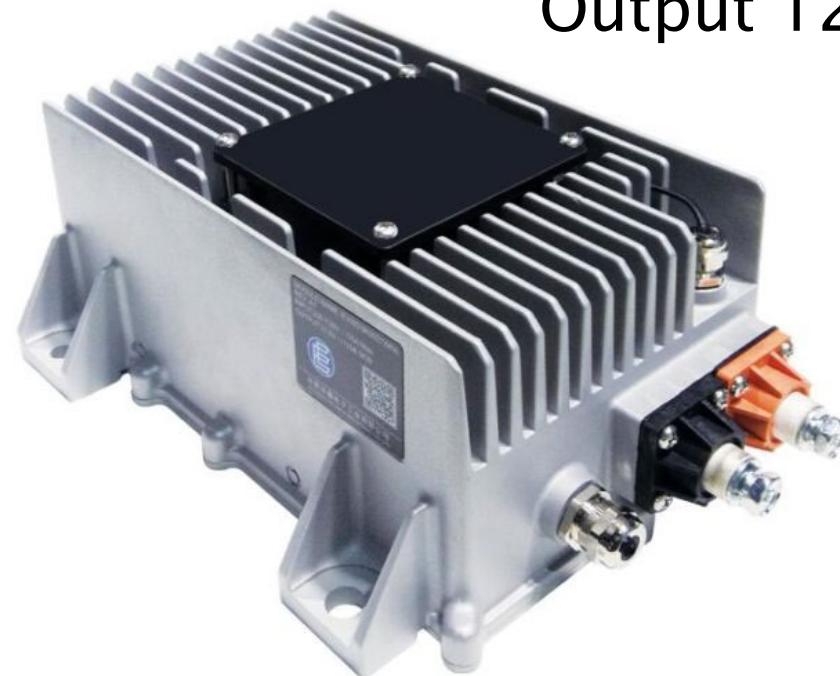
Power 30W

~ £40

<https://www.sunpower-uk.com/>

Sunpower Electronics

Input 200 – 750 V
Output 12 or 24 V



1 kW



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